Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1695	438/197.ccls. or 438/299.ccls. or 438/301.ccls.	USPAT	OR	ON	2005/01/18 09:19
L2	167	((buried adj layer) with (PN adj junction))	USPAT	OR	ON	2005/01/18 09:31
L3	1	("5705842").PN.	USPAT	OR	OFF	2005/01/18 09:31
L4	885	438/286.ccls. or 257/409.ccls.	USPAT	OR	ON	2005/01/18 09:32
L5	449	(438/286.ccls. or 257/409.ccls.) and (breakdown or (break adj down))	USPAT	OR	ON	2005/01/18 09:32
S1	1632	438/197.ccls. or 438/299.ccls. or 438/301.ccls.	USPAT	OR	ON	2005/01/18 09:18
S2	146	semiconductor and drain and source and (gate adj electrode) and (gate adj insulation) and buried and (PN adj junction)	USPAT	OR	ON	2004/10/25 18:30
S3	2	(high adj impurity) and (low adj impurity) and gate and ((buried adj layer) with (PN adj junction))	USPAT	OR	ON	2004/10/25 18:32
S4	162	((buried adj layer) with (PN adj junction))	USPAT	OR	ON	2005/01/18 09:21
S5	862	438/286.ccls. or 257/409.ccls.	USPAT	OR	ON	2005/01/18 09:32
S6	437	(438/286.ccls. or 257/409.ccls.) and (breakdown or (break adj down))	USPAT	OR	ON	2005/01/18 09:32
S7	145	(438/286.ccls. or 257/409.ccls.) and (PN adj junction)	USPAT	OR	ON	2004/10/26 18:19
S8	7606	((break adj down) or breakdown) and (MOS with transistor)	USPAT	OR	ON	2004/10/26 18:20
S9	1442	(((break adj down) or breakdown) and (MOS with transistor)) and (PN adj junction)	USPAT	OR	ON	2004/10/26 18:20
S10	4713	(((break adj down) or breakdown) and (MOS with transistor)) and ((p adj type) or (p-type))	USPAT	OR	ON	2004/10/26 18:21
S11	4553	((((break adj down) or breakdown) and (MOS with transistor)) and ((p adj type) or (p-type))) and gate	USPAT	OR	ON	2004/10/26 18:21
S12	4204	(((((break adj down) or breakdown) and (MOS with transistor)) and ((p adj type) or (p-type))) and gate) and (source and drain)	USPAT	OR	ON	2004/10/28 21:07
S13	2481	((((((break adj down) or breakdown) and (MOS with transistor)) and ((p adj type) or (p-type))) and gate) and (source and drain)) and (impurity)	USPAT	OR	ON	2004/10/26 18:22

S14	12	((((((break adj down) or breakdown) and (MOS with transistor)) and ((p adj type) or (p-type))) and gate) and (source and drain)) and (impurity)) and ((source or drain) with engineering)	USPAT	OR	ON	2004/10/26 18:23
S15	1809	((((((break adj down) or breakdown) and (MOS with transistor)) and ((p adj type) or (p-type))) and gate) and (source and drain)) and (impurity)) and ((breakdown or (break adj down)) adj voltage)	USPAT	OR	ON	2004/10/28 21:01
S16	10	(("5397905") or ("5313082") or ("6638827") or ("6531355") or ("6306711") or ("5521105") or ("5485027") or ("5482888") or ("5070377") or ("6489653")).PN.	USPAT; USOCR	OR	OFF	2004/10/28 22:39
S17	3	(("5397905") or ("6638827") or ("6489653")).PN.	USPAT; USOCR	OR	OFF	2004/10/28 22:39